

Test of PDPC radiation hardness

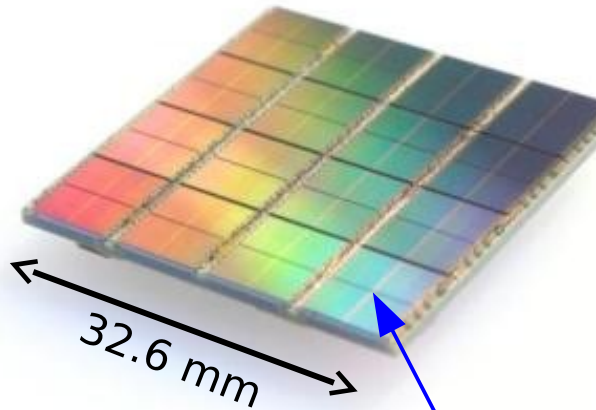
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Outline

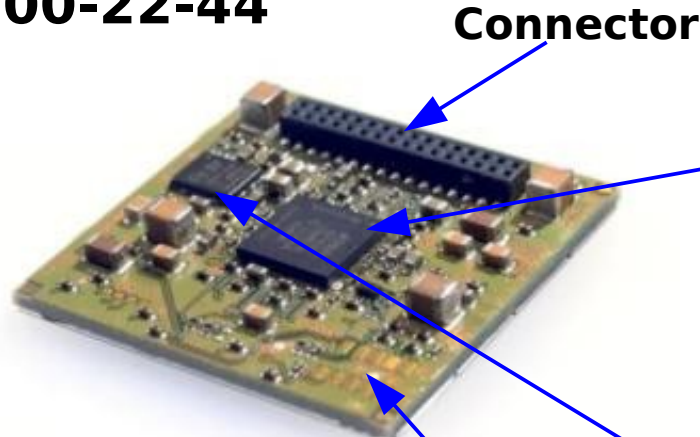
- PDPC
- Test setup
- Analysis and preliminary results

Philips Digital Photon Counter

DPC3200-22-44



4x4 dies



Connector

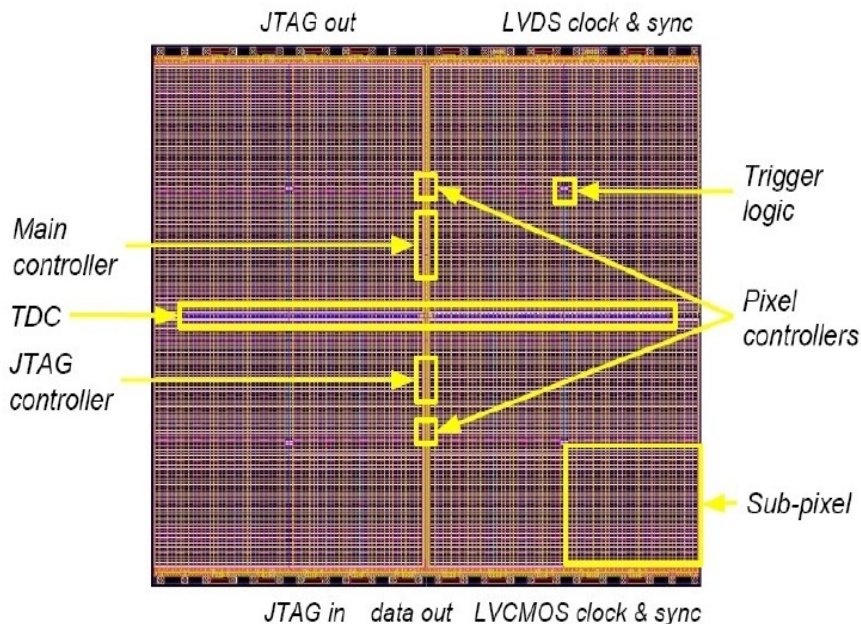
FPGA

- Clock distribution
- Data collection/concentration
- TDC linearization
- Saturation correction
- Skew correction

Temp. sensors

SPI Flash

- FPGA firmware
- Configuration
- Inhibit memory maps



Die

- 2x2 pixels
- TDC
- Logic

Pixel

- 3200 cells (photodiodes) divided in 2x2 subpixels
- Photon counter

Test setup

Proton beam from COSY

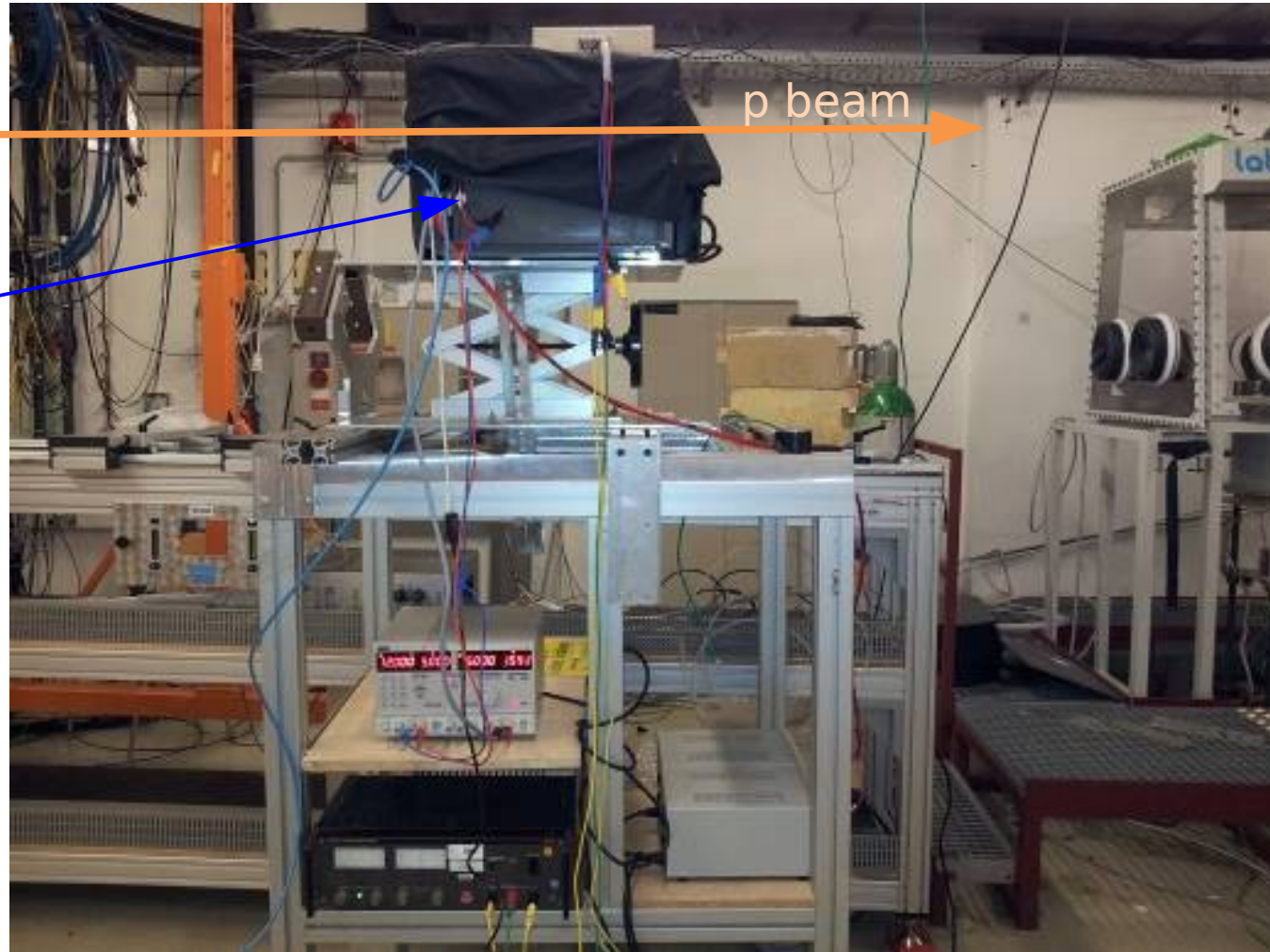
- $P=800$ MeV/c
- Beam size ~ 15 mm
- Intensity up to $2 \cdot 10^7$ s⁻¹

Test box

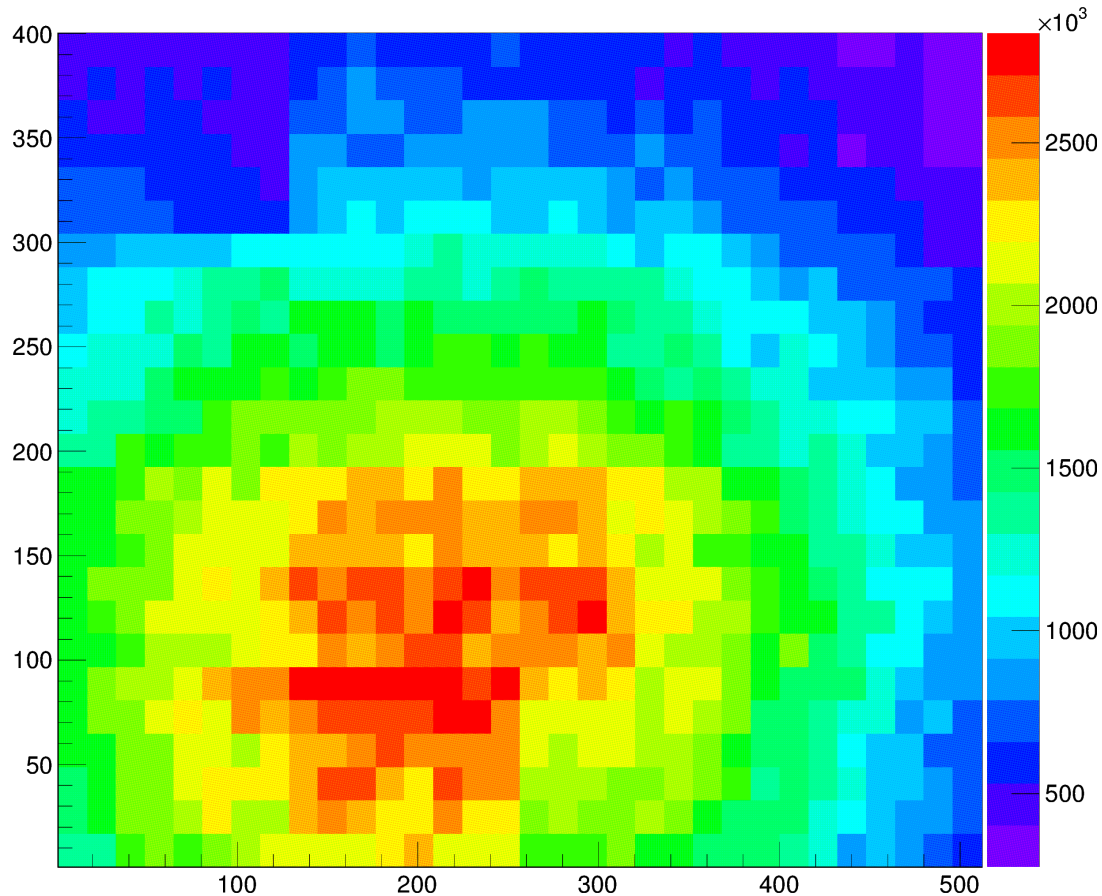
- Two PDPC tiles
- TEK for readout
- Tiles were cooled down to $-15..20^{\circ}\text{C}$

Beam diagnostics

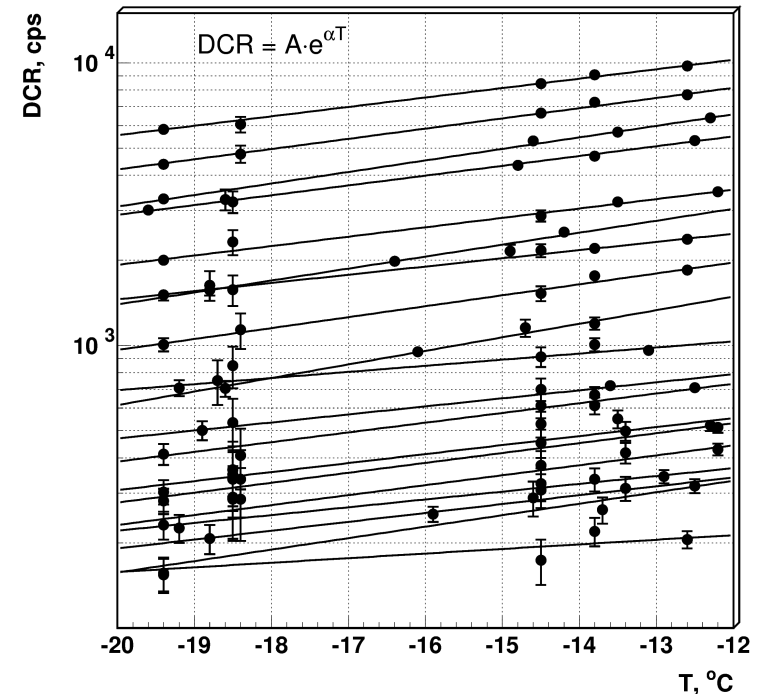
- Ionization chamber (total dose per spill)
- Multi-wire proportional chambers (beam profile)



Dark Counting Rate scan



DCR vs. temperature



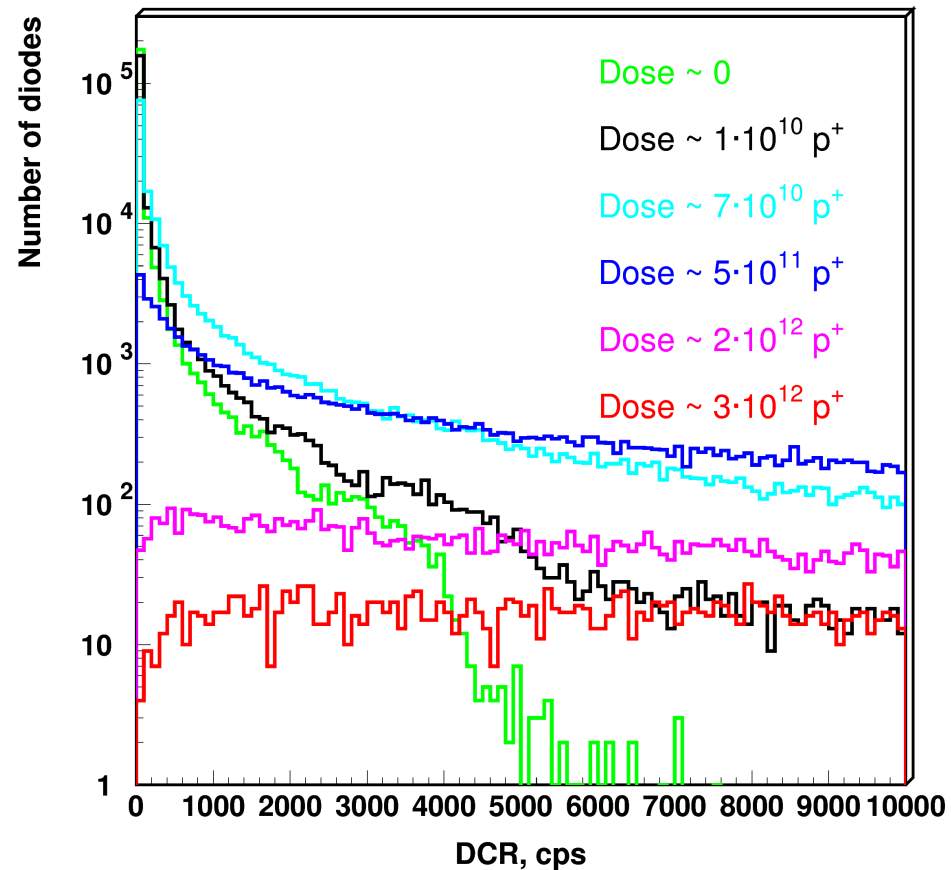
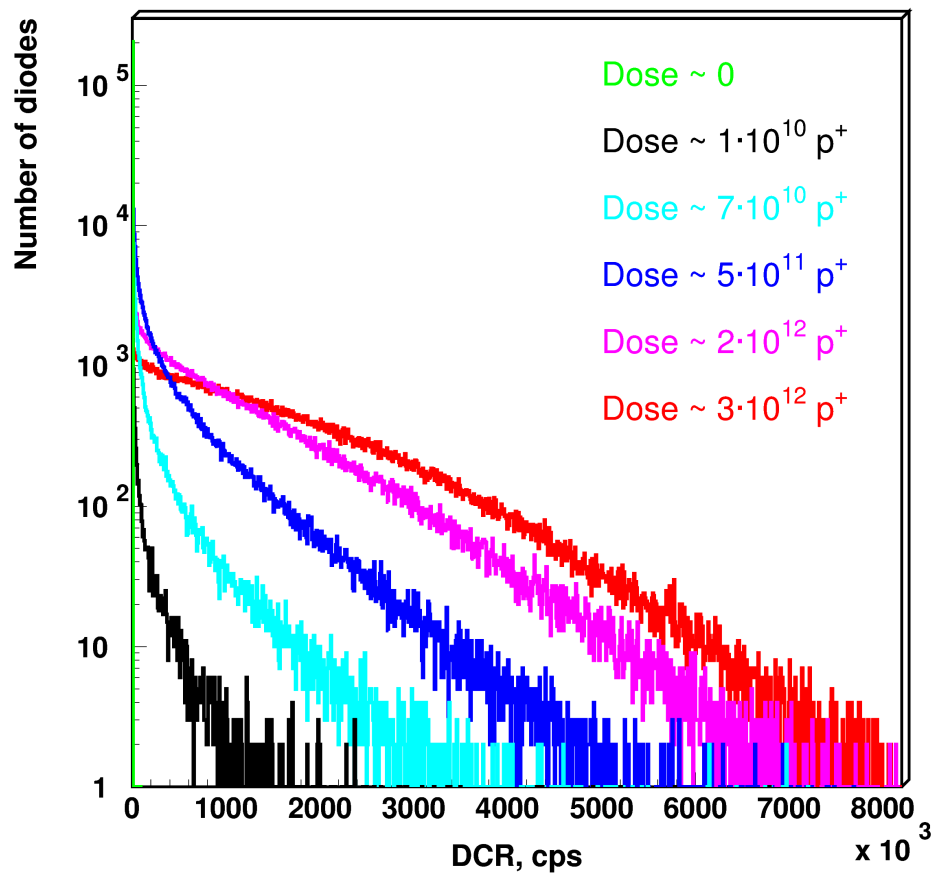
$$\langle \alpha \rangle = 7.86 \cdot 10^{-2} \text{ } ^\circ\text{C}^{-1}$$

DCR changes in 2.2 times per 10°C

All measured rates are reduced to the same temperature (-19°C).

DCR is corrected for the cell dead time = 30..35 ns.

DCR spectra

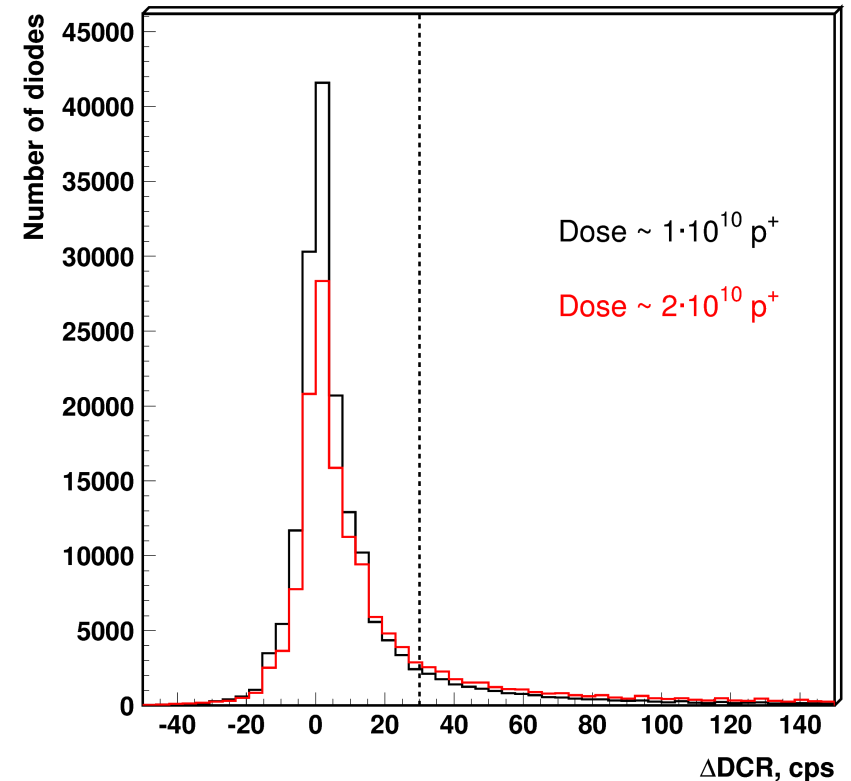
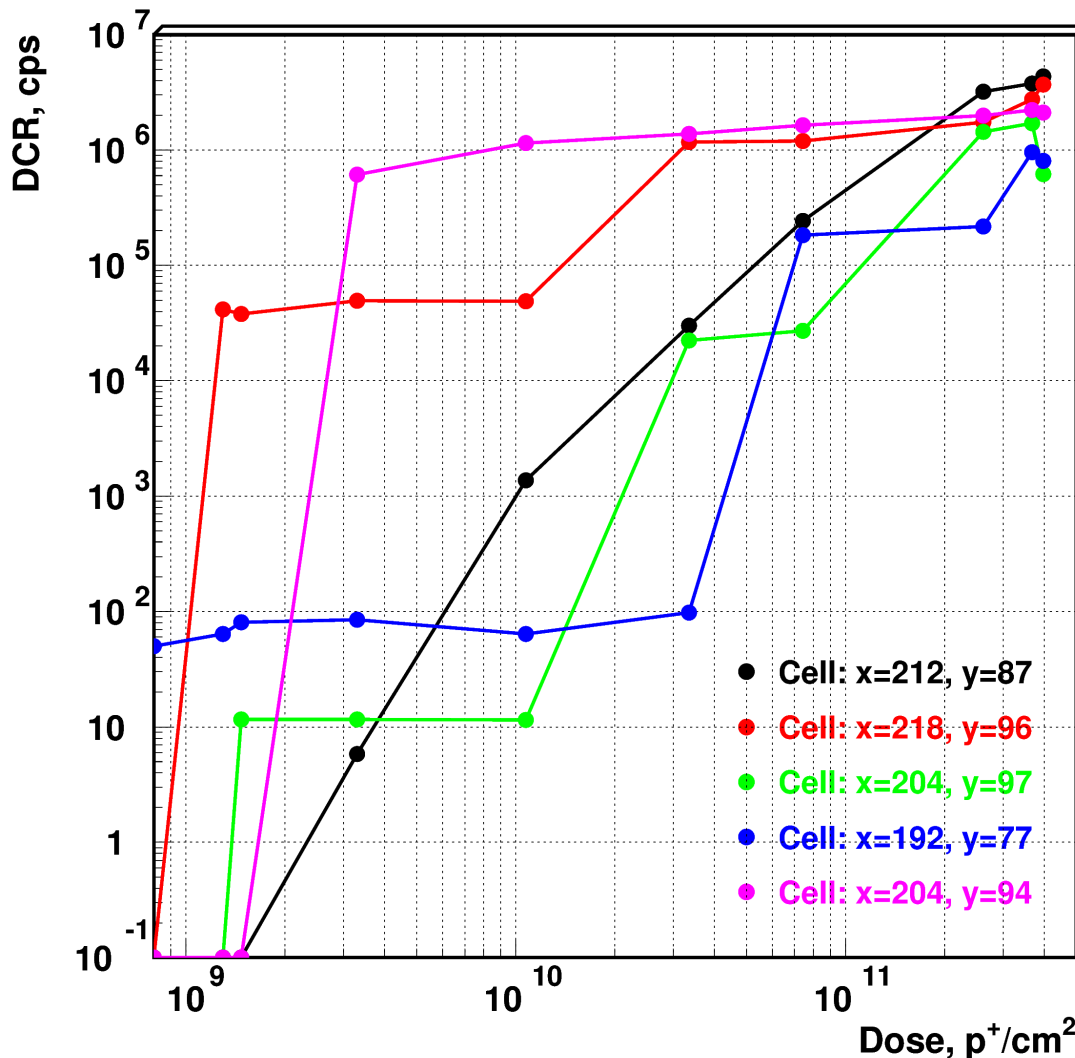


Number of noisy cells increases with total dose.

Single cell DCR

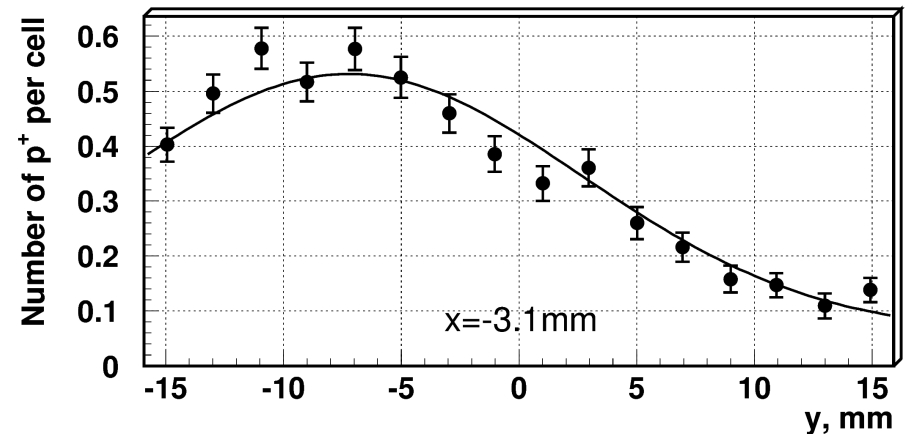
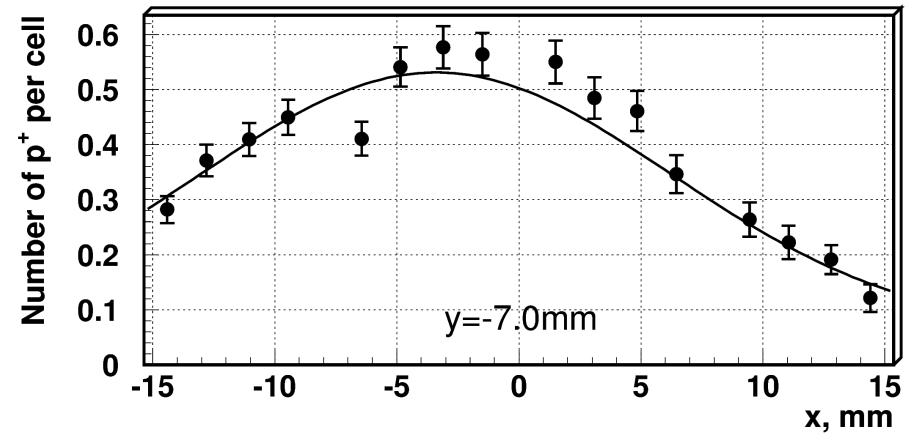
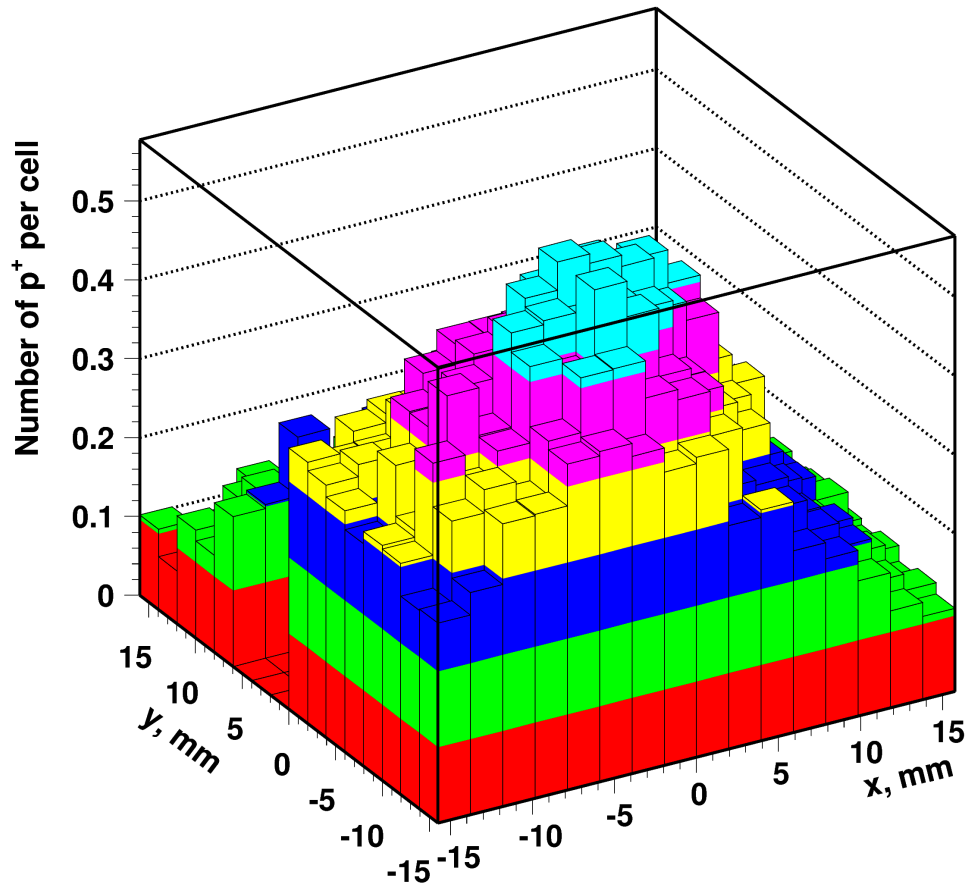
Step-like increase of DCR

=> single interactions of protons with lattice?



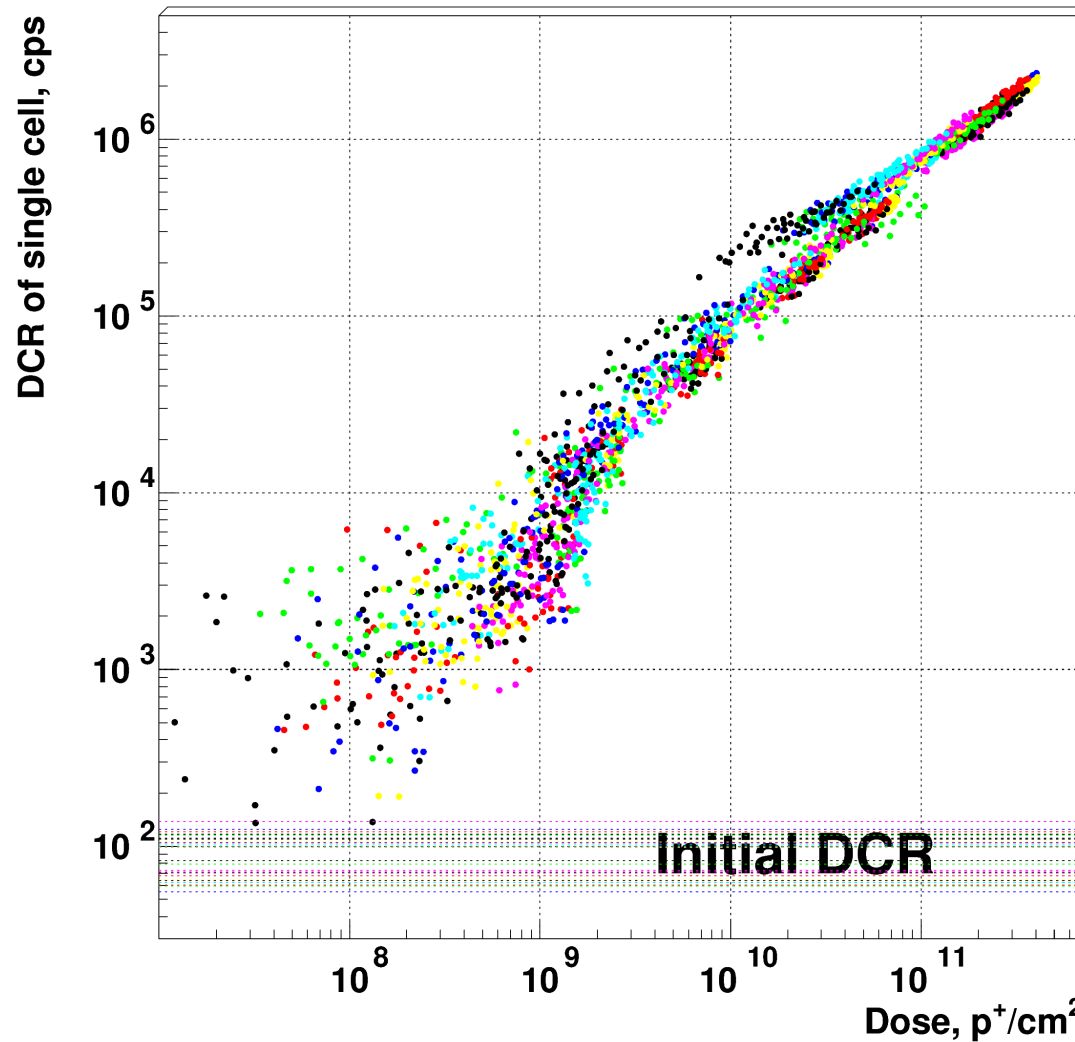
Number of “damaged” cells should be proportional to the proton fluence.

Beam profile estimation



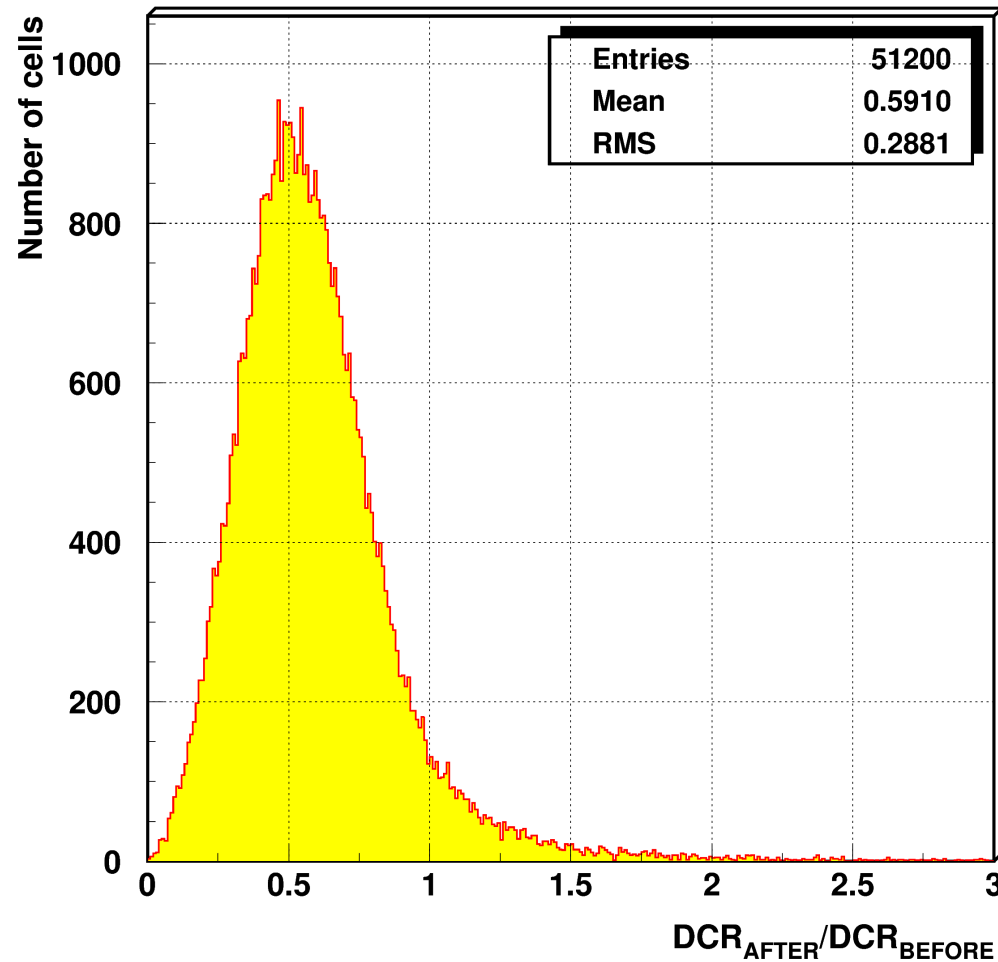
Well fitted by Gaussian + constant.
Origin of the constant is not clear.

DCR vs. proton fluence



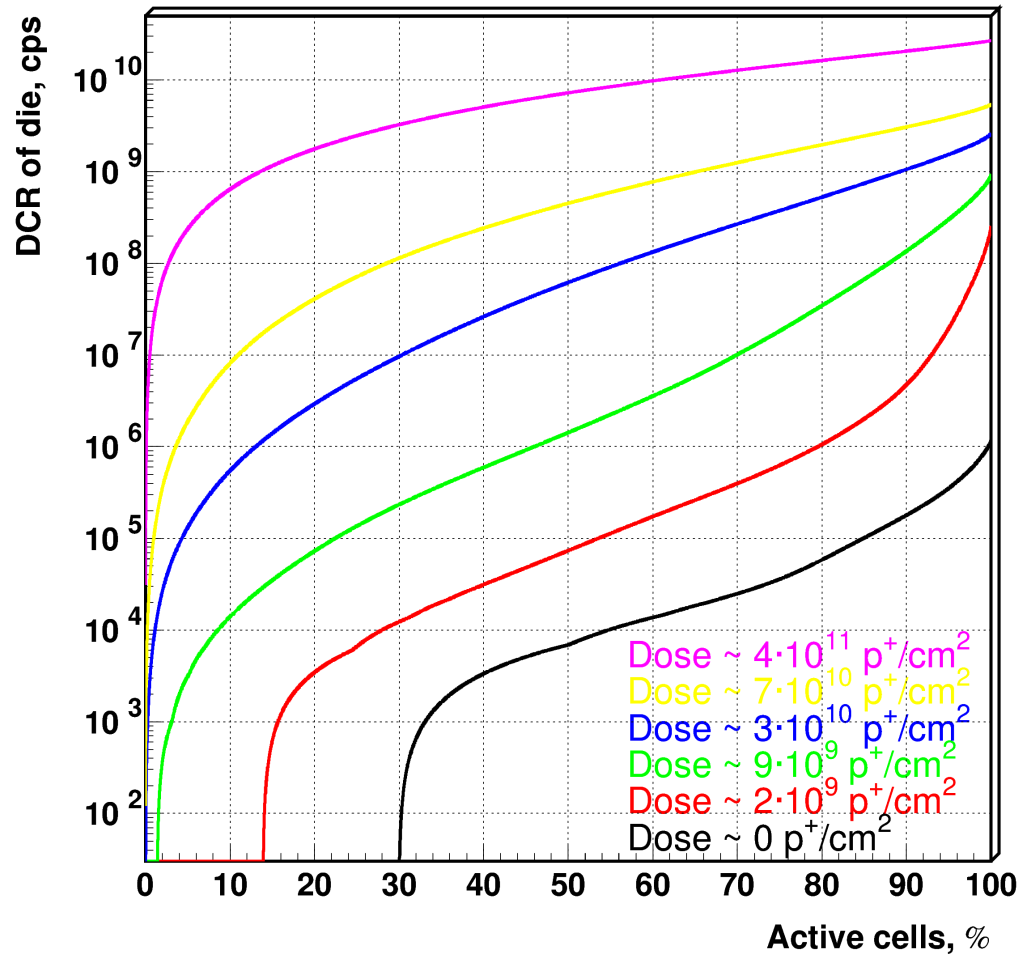
Every point is average DCR for one subpixel (32x25 cells).
Different colors for different dies.

Annealing

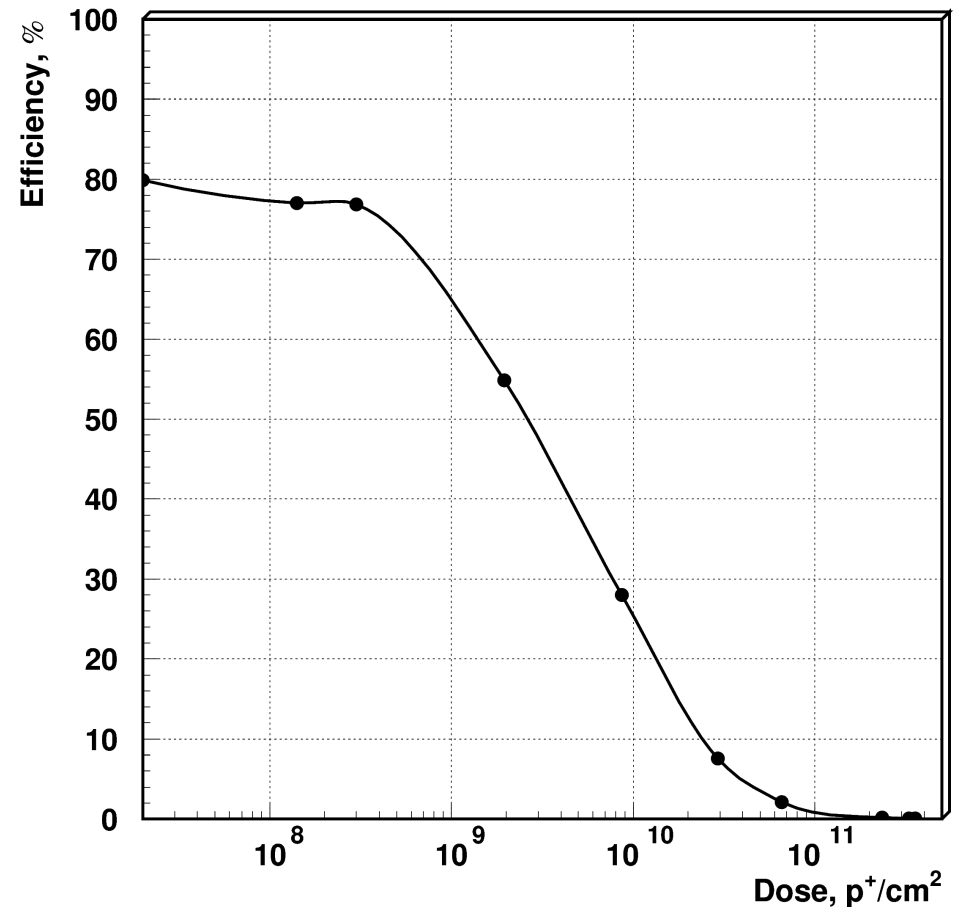


After 8 hours at $T \approx +40^{\circ}\text{C}$ dark rate decreased by 40% on average.

Efficiency degradation



Minimum dead time for current die design is 720 ns.



Optimal efficiency is a tradeoff between number of active cells and dead time due to dark rate.